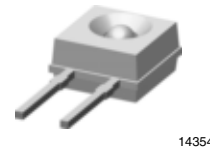


Infrared Emitting Diode, 950 nm, GaAs

Description

TSKS5400S is a standard GaAs infrared emitting diode in a flat sideview molded plastic package. A small recessed spherical lens provides high radiant intensity in a low profile package.

The package is compatible with TEKT5400S phototransistor and TEKS5400 Photo Schmitt Trigger. Assembled on PWB, pairs of emitters and detectors operate as transmissive sensors and reflective sensors.



14354

Features

- High radiant intensity
- Peak wavelength $\lambda_p = 950 \text{ nm}$
- Side view package with spherical lens
- Angle of half sensitivity $\varphi = \pm 30^\circ$



- Package compatible with TEKT5400S and TEKS5400
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

Parts Table

Part	Ordering code	Remarks
TSKS5400S	TSKS5400S	MOQ: 2000 pcs in Plastic Bags
	TSKS5400S-ASZ	MOQ: 2000 pcs, Ammopack, 2.54 mm pin distance (lead to lead), 16 mm height of taping

Absolute Maximum Ratings

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	6	V
Forward current		I_F	100	mA
Surge forward current	$t_p \leq 100 \mu\text{s}$	I_{FSM}	2	A
Power dissipation		P_V	170	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5 \text{ s}$, 2 mm from body	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient		R_{thJA}	450	k/W

Basic Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 100\text{ mA}$, $t_p \leq 20\text{ ms}$	V_F		1.3	1.7	V
Reverse voltage	$I_R = 10\text{ }\mu\text{A}$	V_R	6			V
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_j		50		pF
Radiant intensity	$I_F = 50\text{ mA}$, $t_p \leq 20\text{ ms}$	I_e	2		7	mW/sr
Radiant power	$I_F = 50\text{ mA}$, $t_p \leq 20\text{ ms}$	ϕ_e		10		mW
Temp. coefficient of ϕ_e	$I_F = 50\text{ mA}$	$TK\phi_e$		- 1.0		%K
Angle of half sensitivity		ϕ		± 30		$^{\circ}$
Peak wavelength	$I_F = 50\text{ mA}$	λ_p		950		nm
Spectral bandwidth	$I_F = 50\text{ mA}$	$\Delta\lambda$		50		nm
Rise time	$I_F = 1\text{ A}$, $t_p/T = 0.01$, $t_p \leq 10\text{ }\mu\text{s}$	t_r		400		ns
Fall time	$I_F = 1\text{ A}$, $t_p/T = 0.01$, $t_p \leq 10\text{ }\mu\text{s}$	t_f		450		ns

Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

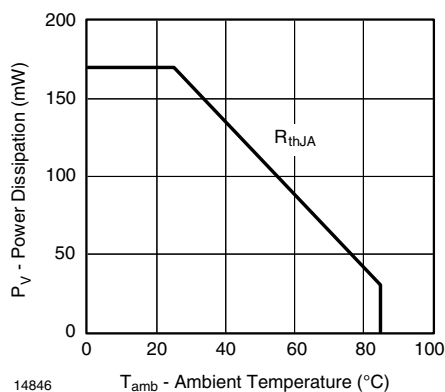


Figure 1. Power Dissipation vs. Ambient Temperature

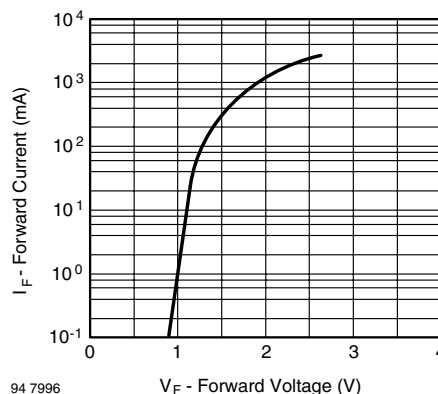


Figure 3. Forward Current vs. Forward Voltage

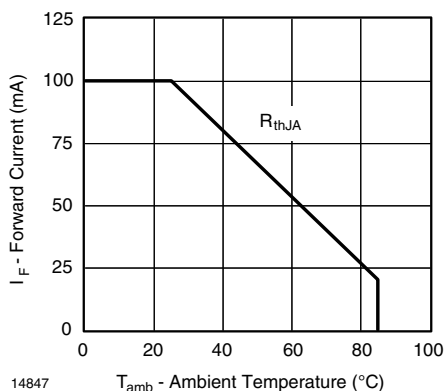


Figure 2. Forward Current vs. Ambient Temperature

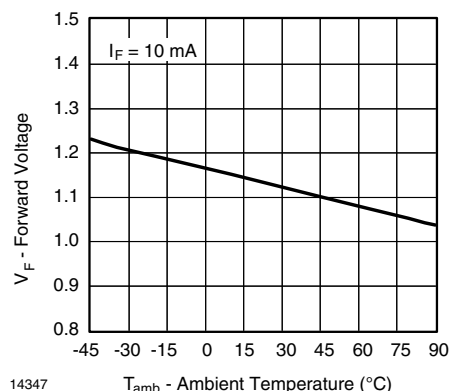
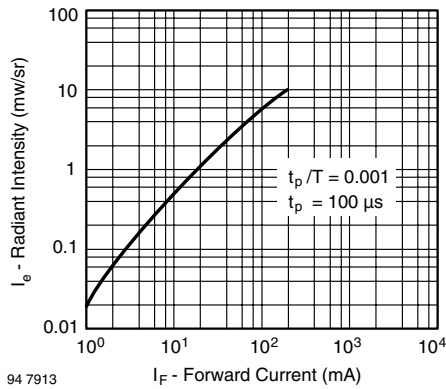
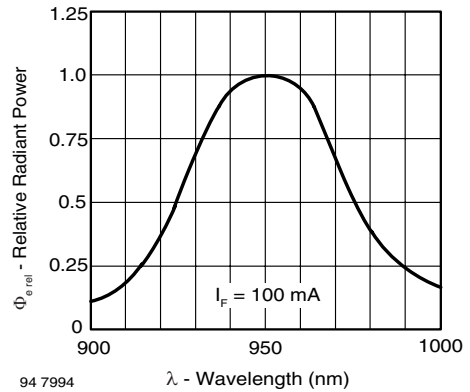


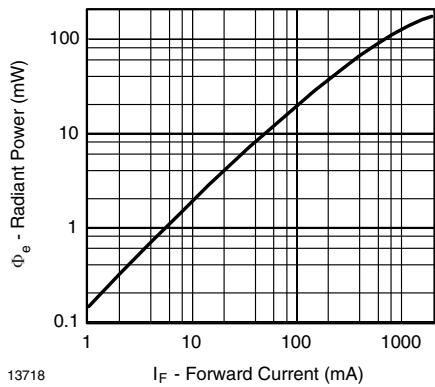
Figure 4. Forward Voltage vs. Ambient Temperature



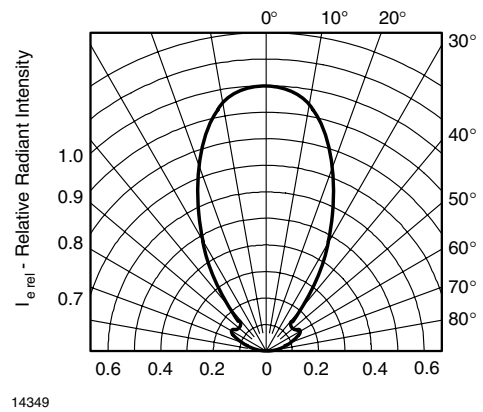
94 7913
Figure 5. Radiant Intensity vs. Forward Current



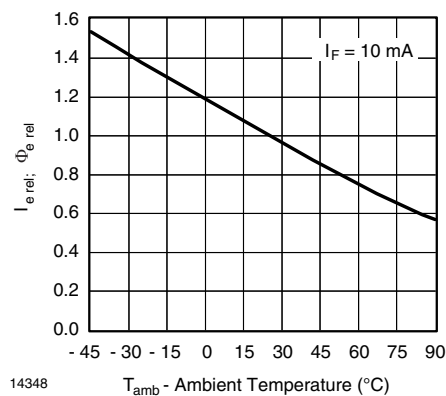
94 7994
Figure 8. Relative Radiant Power vs. Wavelength



13718
Figure 6. Radiant Power vs. Forward Current



14349
Figure 9. Relative Radiant Intensity vs. Angular Displacement



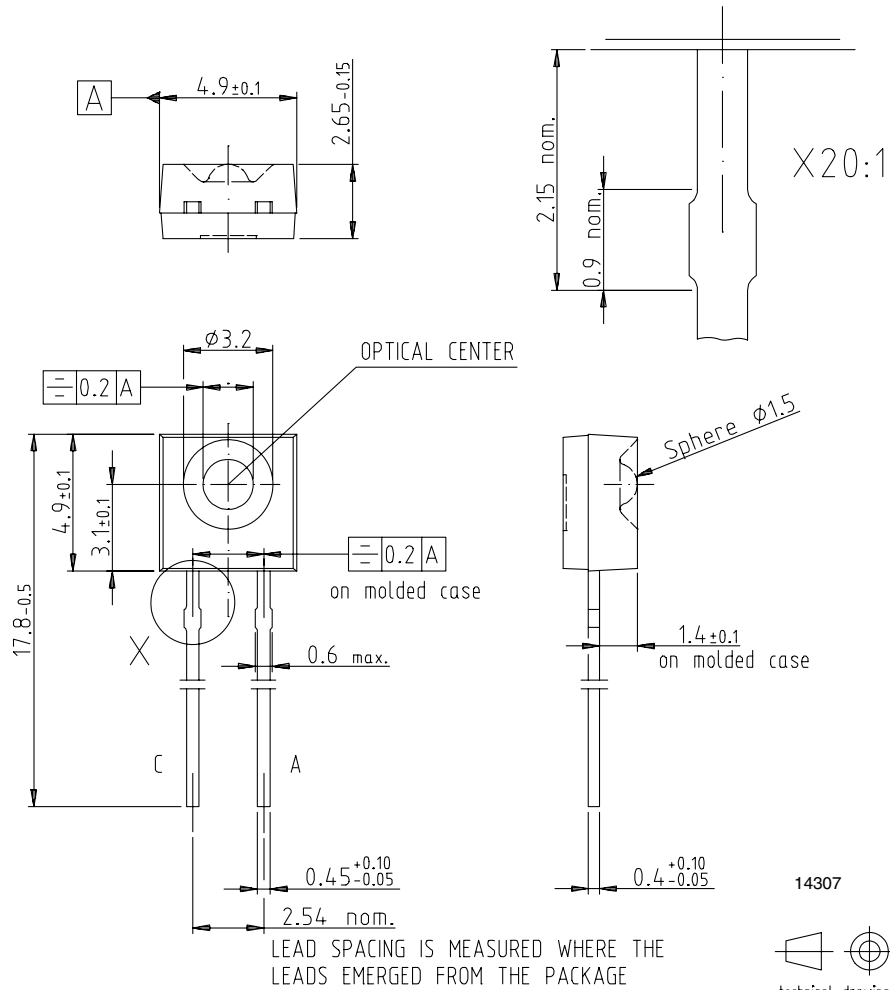
14348
Figure 7. Relative Radiant Intensity vs. Ambient Temperature

TSKS5400S

Vishay Semiconductors

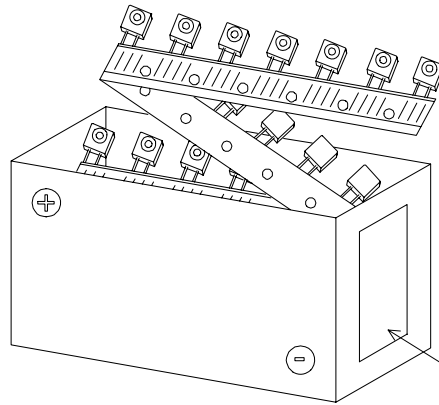


Package Dimensions in mm

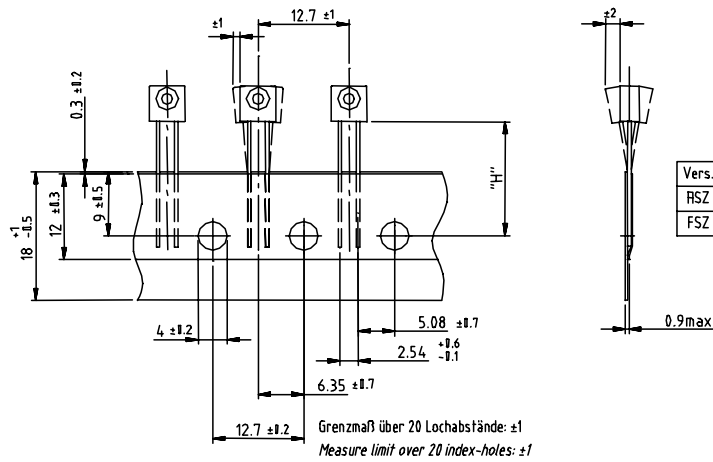


PROTRUDED RESIN AREA WHERE THE LEADS EMERGED FROM THE PACKAGE 0.8 max.

Tape and Ammopack Standards



Kennzeichnung: Barcode-Etikett siehe 5.6.4
Labeling: Barcode-label see 5.6.4



16716

Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Infrared Emitters](#) category:

Click to view products by [Vishay](#) manufacturer:

Other Similar products are found below :

[LTE-309](#) [LTE-3279K](#) [LTE-4206C](#) [LTE-4208C](#) [EAILP03RDAA6](#) [LTE-2871C](#) [LTE-4238](#) [ASDL-4264-C22](#) [OED-EL305F4C50-HT](#) [OP216-004](#) [LTE-3376](#) [EEL109](#) [HL-PST-1608IR1C-L4](#) [SFH 7016](#) [IN-S126ETIR](#) [IN-S126DSHIR](#) [IN-S126ETHIR](#) [IN-P32ZTHIR](#) [IN-S42CTQHIR](#) [IN-S126BTHIR](#) [IN-S63DTHIR](#) [IN-S85BTHIR](#) [IN-S63FTHIR](#) [EAIST3535A1](#) [EAIST3535A4](#) [MHT153IRCT](#) [MHS153IRCT](#) [HIR204C/H0](#) [HIR323C](#) [LTE-209](#) [IR12-21C/TR8](#) [IR17-21C/TR8](#) [IR26-21C/L110/TR8](#) [IR91-21C/TR10](#) [KM-4457F3C](#) [L-53F3BT](#) [WP3A10F3C](#) [LTE-4208](#) [OP235W](#) [IR42-21C/TR8](#) [HSDL-4261](#) [APA3010F3C-GX](#) [SE2460-140](#) [OP266-905](#) [OP280D](#) [LTE-2871](#) [HIR8323/C16](#) [KP-2012SF4C](#) [KPA-3010F3C](#) [L-7113SF6C](#)